Preliminary data sheet

1. General description

Passivated sensitive gate Silicon Controlled Rectifier (SCR) in a SOT428 (DPAK) surface mountable plastic package intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct interfacing with low power drivers and microcontrollers
- High bidirectional blocking voltage capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Sensitive gate for logic level control

3. Applications

- General purpose switching and phase control
- Ignition circuits, CDI for 2- and 3-wheelers
- Motor control e.g. small kitchen appliances Protection circuits for Switched-Mode Power Supplies (SMPS)
- · Protection circuits in lighting ballasts

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|--|---|-----|-----|-----|------|
| V_{DRM} | repetitive peak off- state voltage | | - | - | 650 | V |
| V _{RRM} | repetitive peak reverse voltage | | _ | - | 650 | V |
| I _{TSM} | non-repetitive peak on- state current | half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms | - | - | 90 | Α |
| I _{T(AV)} | average on-state current | half sine wave; T _{mb} ≤ 103 °C; <u>Fig. 1</u> | - | - | 7.5 | А |
| I _{T(RMS)} | RMS on-state current | half sine wave; T _{mb} ≤ 103 °C; <u>Fig. 2</u> | - | - | 12 | А |





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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------|------------------------|--|--|-----|-----|-----|------|
| Static characte | Static characteristics | | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 5$ | | 20 | 50 | 200 | μA |

5. Pinning information

Table 2. Pinning information

| 1 K 2 A 3 G | cathode anode gate | mb | A - K G sym037 |
|-------------|-----------------------------------|--------------------|------------------------|
| | | | |
| 3 G | gate | | • |
| | gate | \/ | |
| mb A | mounting base; connected to anode | 1 3 DPAK (SOT428) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|---|---------|
| | Name | Description | Version |
| BT151S-650S | DPAK | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BT151S-650S | BT151S-650S |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|--|-----|-----|------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 650 | V |
| V_{RRM} | repetitive peak reverse voltage | | - | 650 | V |
| I _{T(AV)} | average on-state current | half sine wave; T _{mb} ≤ 103 °C; <u>Fig. 1</u> | - | 7.5 | Α |
| I _{T(RMS)} | RMS on-state current | half sine wave; T _{mb} ≤ 103 °C; <u>Fig. 2</u> | - | 12 | Α |
| I _{TSM} | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 10 \text{ms}$ | - | 90 | А |
| | | half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 \text{ms}$ | - | 100 | Α |
| I ² t | I ² t for fusing | t _p = 10 ms; SIN | - | 41 | A ² s |
| dl _T /dt | rate of rise of on-state current | $I_T = 20 \text{ A}$; $I_G = 50 \text{ mA}$; $dI_G/dt = 50 \text{ mA}/$ µs | - | 50 | A/µs |
| I _{GM} | peak gate current | | - | 2 | Α |
| V_{RGM} | peak reverse gate voltage | | - | 5 | V |
| P_GM | peak gate power | | - | 5 | W |
| P _{G(AV)} | average gate power | over any 20 ms period | - | 0.5 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| Tj | junction temperature | | - | 125 | °C |

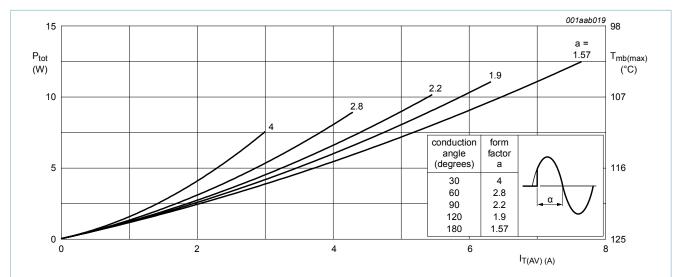


Fig. 1. Total power dissipation as a function of average on-state current; maximum values

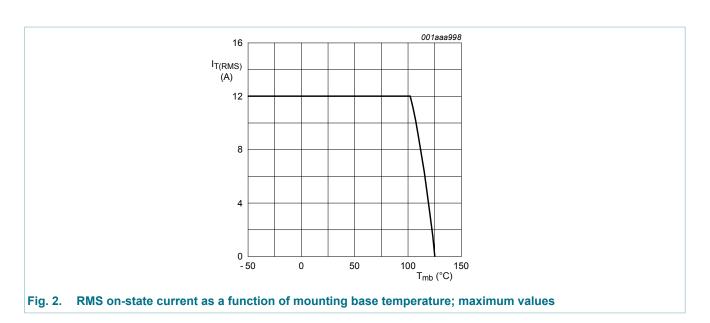
 $a = \text{form factor} = I_{T(RMS)} / I_{T(AV)}$

BT151S-650S

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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|--|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 3 | - | - | 2 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | Device mounted on an FR4 printed- circuit board, single-sided copper, tin- plated and standard footprint; Fig. 4 | - | 7 | - | K/W |

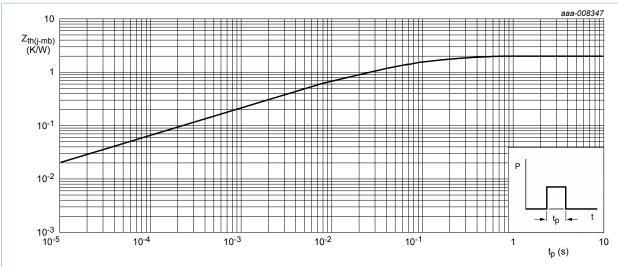
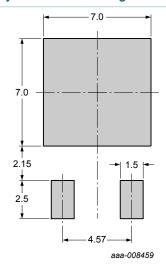


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width



All dimensions are in mm

Plastic meets requirements of UL94 V-O at 3.175 mm

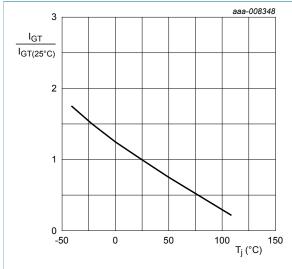
Fig. 4. SOT428: minimum pad sizes for surface-mounting

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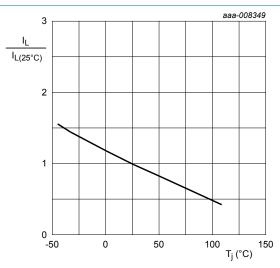
10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|-----------------------------------|--|-----|-----|------|------|
| Static chara | acteristics | | ' | | | |
| I _{GT} | gate trigger current | V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 5</u> | 20 | 50 | 200 | μA |
| IL | latching current | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 6$ | - | 0.4 | 10 | mA |
| I _H | holding current | V _D = 12 V; T _j = 25 °C; <u>Fig. 7</u> | - | 0.3 | 6 | mA |
| V_{T} | on-state voltage | I _T = 20 A; T _j = 25 °C | - | 1.3 | 1.75 | V |
| V_{GT} | gate trigger voltage | V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 8</u> | - | 0.6 | 1 | V |
| | | $V_D = 650 \text{ V}; I_T = 0.1 \text{ A}; T_j = 110 ^{\circ}\text{C};$ Fig. 8 | 0.1 | 0.2 | - | V |
| I _D | off-state current | V _D = 650 V; T _j = 125 °C | - | 0.1 | 0.5 | mA |
| I _R | reverse current | V _R = 650 V; T _j = 125 °C | - | 0.1 | 0.5 | mA |
| Dynamic cl | harateristics | | ' | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 436 V; T_j = 125 °C; R_{GK} = 100 Ω; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; Fig. 9 | 50 | 100 | - | V/µs |



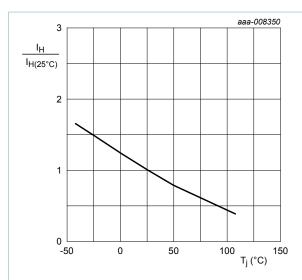




Normalized latching current as a function of junction temperature

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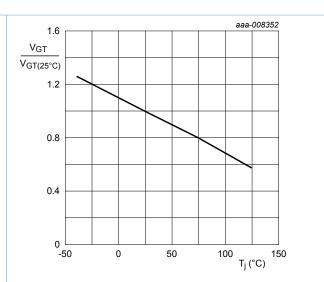


Fig. 7. Normalized holding current as a function of junction temperature

Fig. 8. Normalized gate trigger voltage as a function of junction temperature

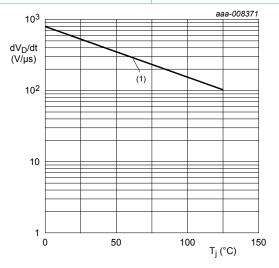


Fig. 9. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

(1) R_{GK} = 100 Ω

11. Package outline

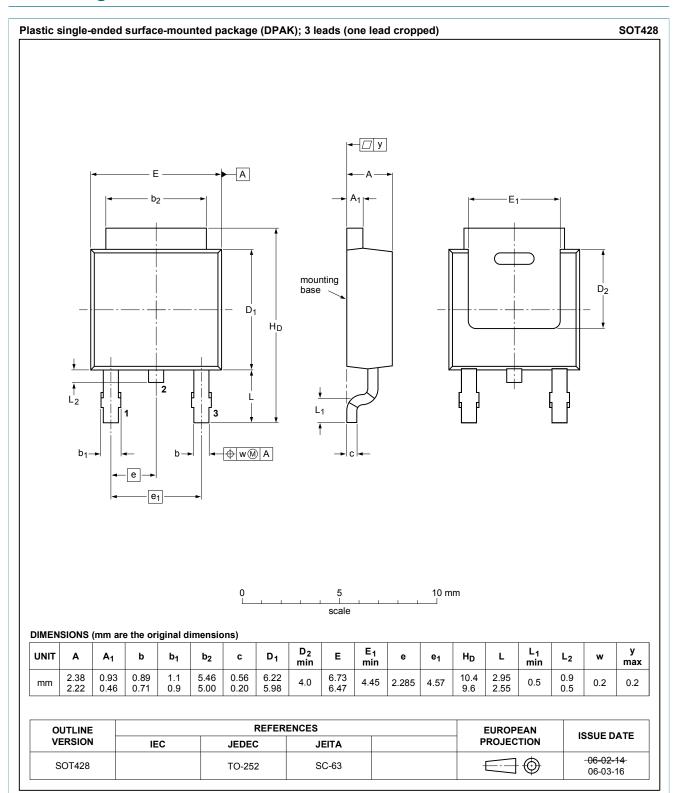


Fig. 10. Package outline DPAK (SOT428)

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12. Legal information

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|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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